

# NST847BPDP6T5G

## Dual Complementary General Purpose Transistor

The NST847BPDP6T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-963 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

### Features

- $h_{FE}$ , 200–450
- Low  $V_{CE(sat)}$ ,  $\leq 0.3$  V
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- This is a Pb-Free Device

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	45	Vdc
Collector – Base Voltage	$V_{CB0}$	50	Vdc
Emitter – Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous	$I_C$	100	mAdc
Electrostatic Discharge	HBM MM	ESD Class	2 B

### THERMAL CHARACTERISTICS

Characteristic (Single Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 1)	$P_D$	240 1.9	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	520	$^\circ\text{C}/\text{W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 2)	$P_D$	280 2.2	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	446	$^\circ\text{C}/\text{W}$
Characteristic (Dual Heated) (Note 3)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 1)	$P_D$	350 2.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 2)	$P_D$	420 3.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	297	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

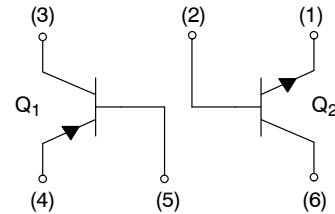
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
2. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.
3. Dual heated values assume total power is sum of two equally powered channels



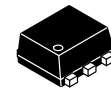
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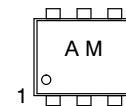
NST847BPDP6T5G\*

\*Q1 PNP  
Q2 NPN



SOT-963  
CASE 527AD

### MARKING DIAGRAM



A = Device Code  
M = Date Code

### ORDERING INFORMATION

Device	Package	Shipping†
NST847BPDP6T5G	SOT-963 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NST847BPDP6T5G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0) (I <sub>C</sub> = -1.0 mA, I <sub>B</sub> = 0)	(NPN) (PNP)	V <sub>(BR)CEO</sub>	45 -45	- -	V
Collector–Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0) (I <sub>C</sub> = -10 μA, I <sub>E</sub> = 0)	(NPN) (PNP)	V <sub>(BR)CBO</sub>	50 -50	- -	V
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 10 μA) (I <sub>C</sub> = -10 μA)	(NPN) (PNP)	V <sub>(BR)CES</sub>	50 -50	- -	V
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 1.0 μA, I <sub>C</sub> = 0) (I <sub>E</sub> = -1.0 μA, I <sub>C</sub> = 0)	(NPN) (PNP)	V <sub>(BR)EBO</sub>	6.0 -5.0	- -	V
Collector Cutoff Current (V <sub>CB</sub> = 30 V) (V <sub>CB</sub> = 30 V, T <sub>A</sub> = 150°C) (V <sub>CB</sub> = -30 V) (V <sub>CB</sub> = -30 V, T <sub>A</sub> = 150°C)	(NPN) (NPN) (PNP) (PNP)	I <sub>CBO</sub>	- - - -	- - - -	nA μA nA μA

## ON CHARACTERISTICS (Note 4)

DC Current Gain (I <sub>C</sub> = 2.0 mA, V <sub>CE</sub> = 5.0 V)  (I <sub>C</sub> = -2.0 mA, V <sub>CE</sub> = -5.0 V)	(NPN)  (PNP)	h <sub>FE</sub>	200  220	290  290	450  475	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.5 mA) (I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5.0 mA)  (I <sub>C</sub> = -10 mA, I <sub>B</sub> = -0.5 mA) (I <sub>C</sub> = -100 mA, I <sub>B</sub> = -5.0 mA)	(NPN)  (PNP)	V <sub>CE(sat)</sub>	- -  -	- -  -	0.25 0.60  -0.30 -0.70	V
Base–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.5 mA) (I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5.0 mA)  (I <sub>C</sub> = -10 mA, I <sub>B</sub> = -0.5 mA) (I <sub>C</sub> = -100 mA, I <sub>B</sub> = -5.0 mA)	(NPN)  (PNP)	V <sub>BE(sat)</sub>	- -  -	0.70 0.90  -0.70 -0.90	- -  -	V
Base–Emitter On Voltage (I <sub>C</sub> = 2.0 mA, V <sub>CE</sub> = 5.0 V) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V)  (I <sub>C</sub> = -2.0 mA, V <sub>CE</sub> = -5.0 V) (I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -5.0 V)	(NPN)  (PNP)	V <sub>BE(on)</sub>	0.58 -  -0.60 -	0.66 -  -	0.70 0.77  -0.75 -0.82	V

## SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V, f = 100 MHz)  (I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -5.0 V, f = 100 MHz)	(NPN)  (PNP)	f <sub>T</sub>	100  100	-  -	-  -	MHz
Output Capacitance (V <sub>CB</sub> = 10 V, f = 1.0 MHz)  (V <sub>CB</sub> = -10 V, f = 1.0 MHz)	(NPN)  (PNP)	C <sub>ob</sub>	-  -	-  -	4.5  4.5	pF
Noise Figure (I <sub>C</sub> = 0.2 mA, V <sub>CE</sub> = 5.0 V, R <sub>S</sub> = 2 kΩ, f = 1 kHz, BW = 200 Hz)  (I <sub>C</sub> = -0.2 mA, V <sub>CE</sub> = -5.0 V, R <sub>S</sub> = 2 kΩ, f = 1 kHz, BW = 200 Hz)	(NPN)  (PNP)	NF	-  -	-  -	10  10	dB

4. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

# NST847BPDP6T5G

## NPN TRANSISTOR

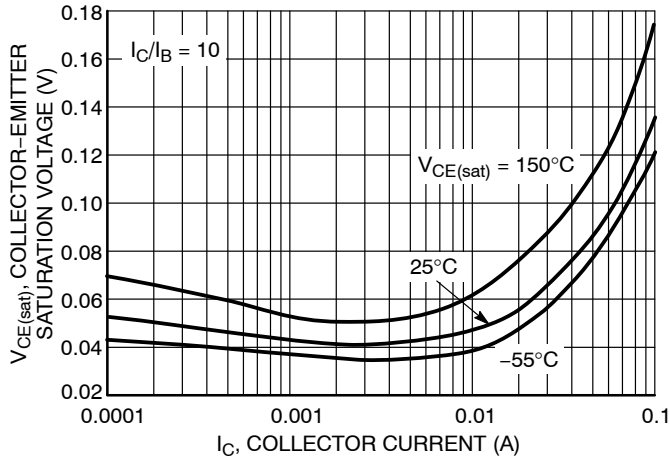


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

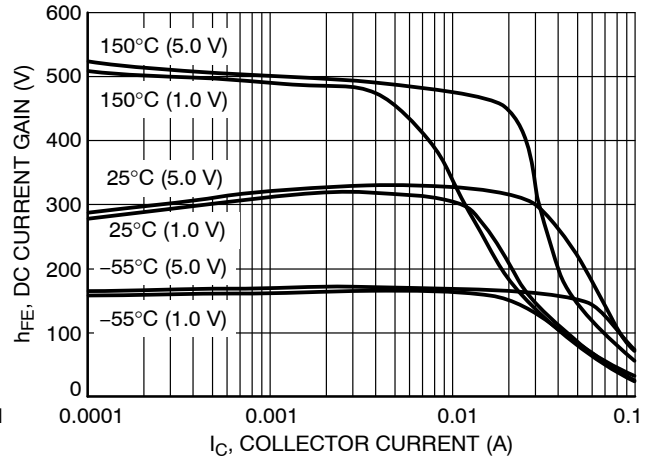
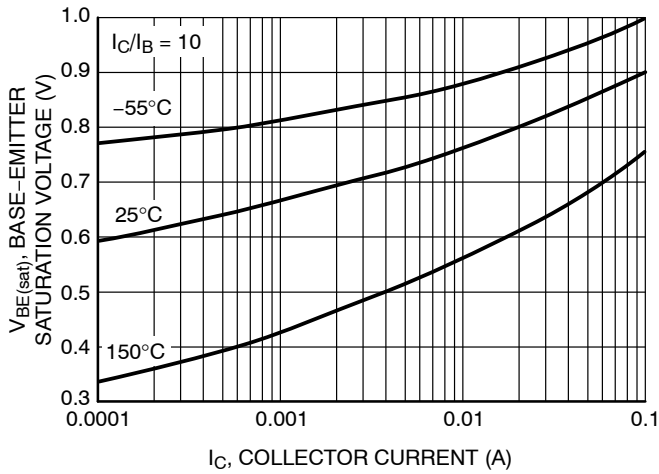


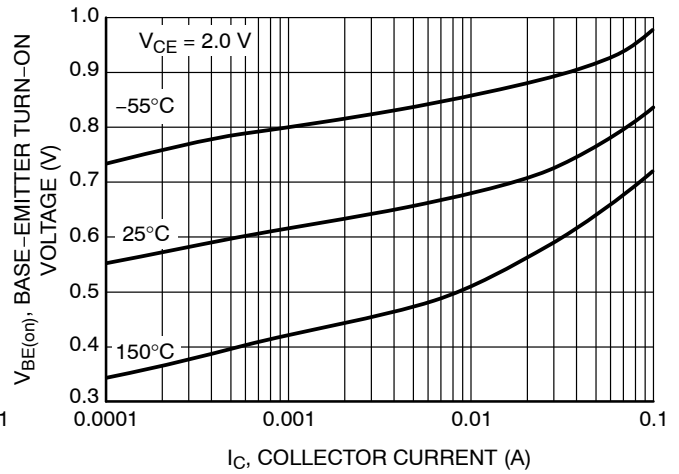
Figure 2. DC Current Gain vs. Collector Current

## NPN TRANSISTOR

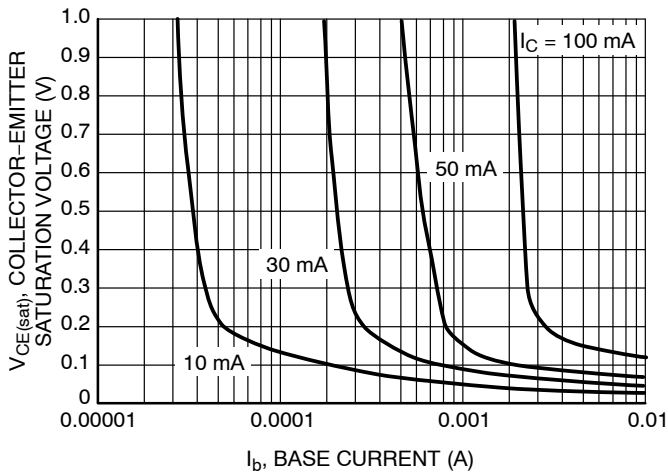
# NST847BPDP6T5G



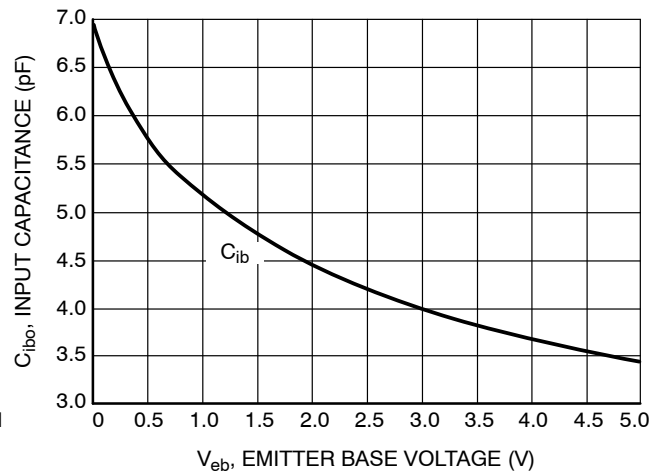
**Figure 3. Base Emitter Saturation Voltage vs. Collector Current**



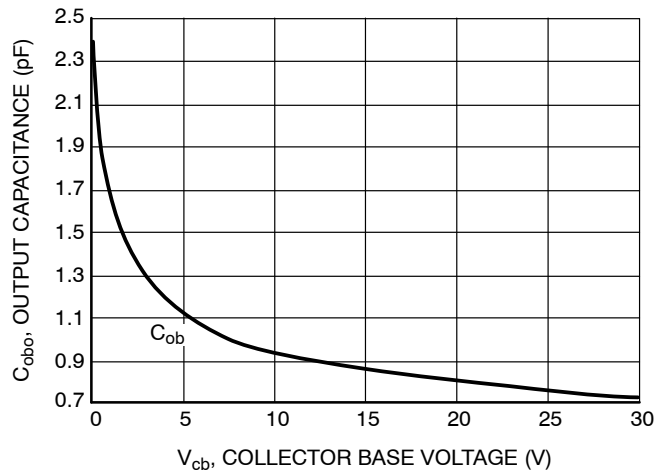
**Figure 4. Base Emitter Turn-On Voltage vs. Collector Current**



**Figure 5. Saturation Region**



**Figure 6. Input Capacitance**



**Figure 7. Output Capacitance**

# NST847BPDP6T5G

## PNP TRANSISTOR

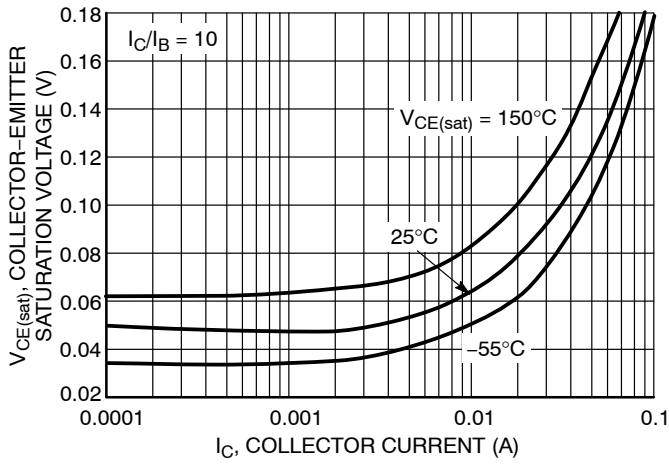


Figure 8. Collector Emitter Saturation Voltage vs. Collector Current

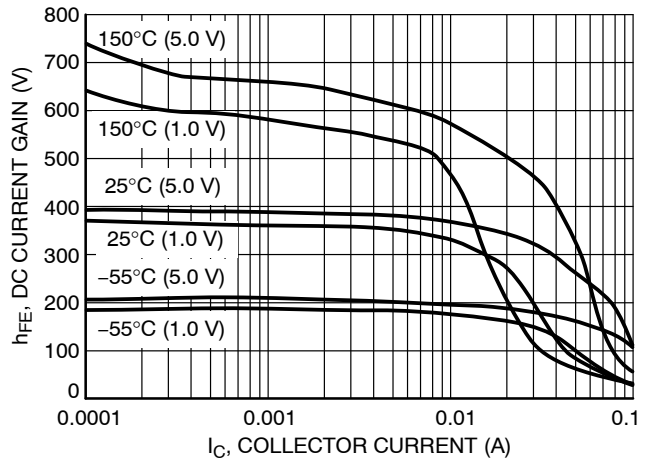
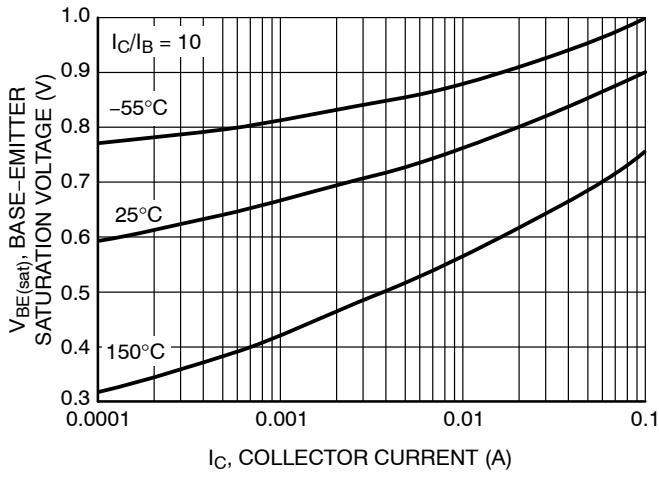


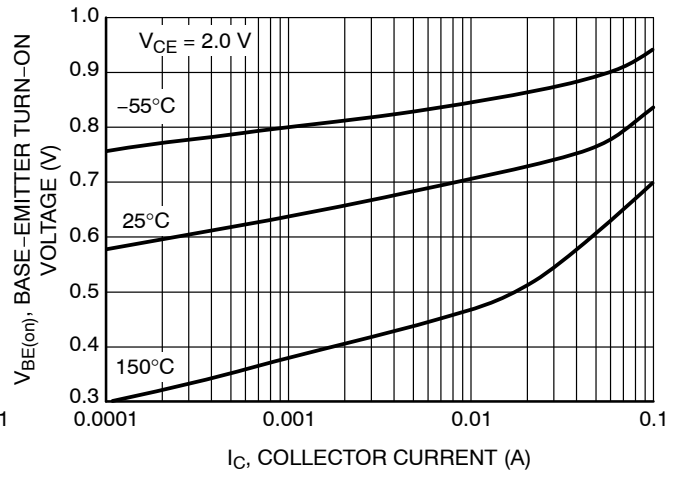
Figure 9. DC Current Gain vs. Collector Current

## PNP TRANSISTOR

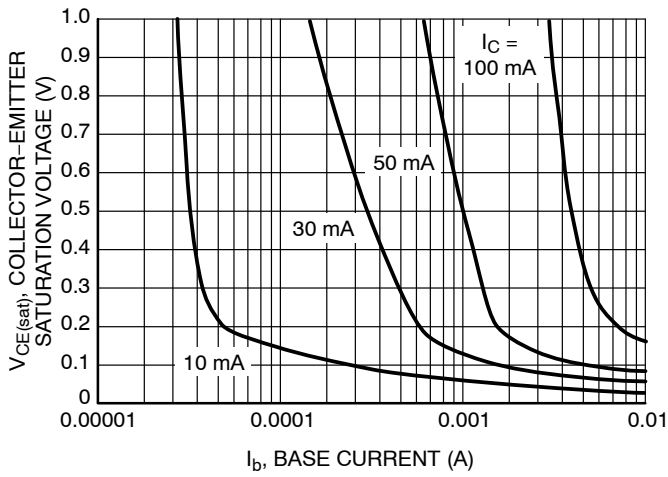
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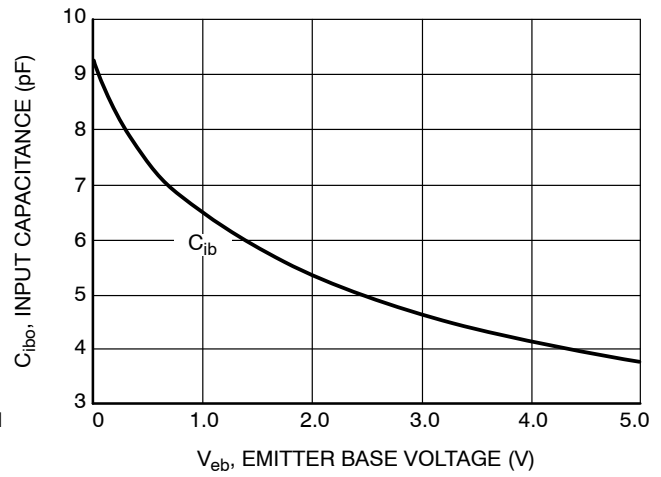
**Figure 10. Base Emitter Saturation Voltage vs. Collector Current**



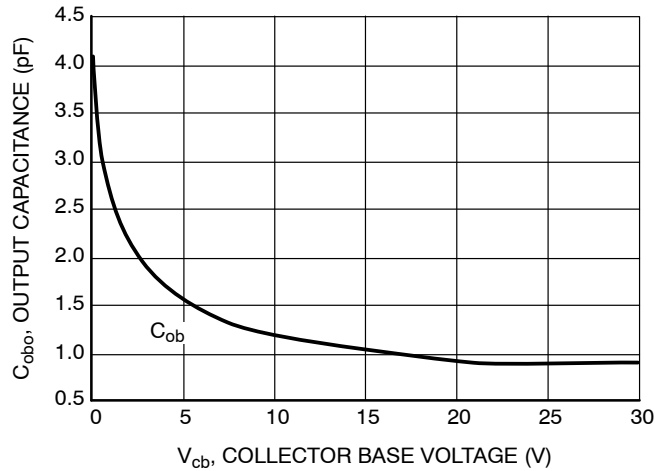
**Figure 11. Base Emitter Turn-On Voltage vs. Collector Current**



**Figure 12. Saturation Region**



**Figure 13. Input Capacitance**

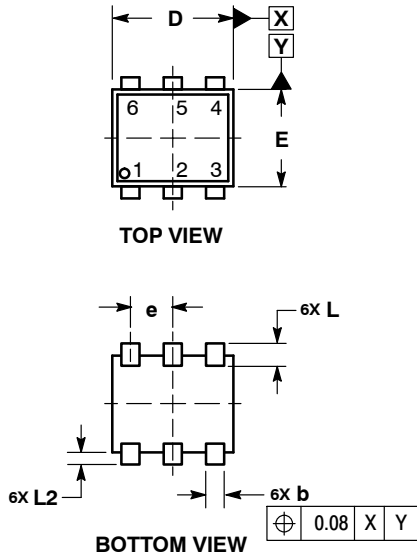


**Figure 14. Output Capacitance**

# NST847BPDP6T5G

## PACKAGE DIMENSIONS

**SOT-963**  
CASE 527AD  
ISSUE E

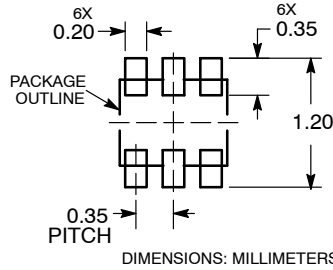


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
He	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15

### RECOMMENDED MOUNTING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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